



01-003

April 9, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/780,416 02/17/04 |

Hsiu-Wen Hsu

METHOD OF FORMING A SEMICONDUCTOR
DEVICE HAVING A CAPACITOR AND A
RESISTOR
| _____ |

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on April 12, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

SB Ackerman 4/12/04

U.S. Patent 6,246,084 to Kim, "Method for Fabricating Semiconductor Device Comprising Capacitor and Resistor," describes a method for fabricating a capacitor and resistor over a shallow trench isolation (STI) structure.

U.S. Patent 5,618,749 to Takahashi et al., "Method of Forming a Semiconductor Device Having a Capacitor and a Resistor," describes a method for fabricating a capacitor and resistor over a shallow trench isolation (STI) structure.

U.S. Patent 5,434,098 to Chang, "Double Poly Process with Independently Adjustable Interpoly Dielectric Thickness," describes a capacitor process with an interpoly oxide (IPO) layer.

U.S. Patent 5,656,524 to Eklund et al., "Method of Forming a Polysilicon Resistor Using an Oxide, Nitride Stack," describes a method of forming a polysilicon resistor.

Sincerely,

A handwritten signature in black ink, appearing to read 'SBA', with a large, stylized circular flourish to the right.

Stephen B. Ackerman,
Reg. No. 37761

Doc No: (Copy No)

Agreement Number

Logically

Filing Date

02/17/04

Group Art Unit

EXAMINER
INITIAL

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WBCLES

PLANO DATE
X APPROPRIATE

Kim

257

296

11/10/98

56187494/8/9-

Takahashi et al.

438

384

3/31/95

54340987/18/95

Change

437

60

6/3/94

56565248/12/9-

Ekund et al.

438

238

6/7/95

DOCUMENT NUMBER

DATE

COUNTRY

CLASS

SUBCLASS

Translation

YES

NO

αλυσίδα

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.